Dual 2-Input NAND Gate

The NL27WZ00 is a high performance dual 2-input NAND Gate operating from a 1.65 V to 5.5 V supply.

Features

- Extremely High Speed: t_{PD} 2.4 ns (typical) at $V_{CC} = 5.0 \text{ V}$
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- Over Voltage Tolerant Inputs
- LVTTL Compatible Interface Capability With 5.0 V TTL Logic with $V_{CC} = 3.0 \text{ V}$
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- Replacement for NC7WZ00
- Chip Complexity: FET = 112
- Pb-Free Package is Available

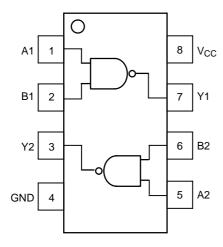


Figure 1. Pinout

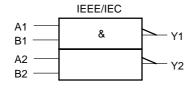


Figure 2. Logic Symbol



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US8 US SUFFIX CASE 493



MARKING

L1 = Specific Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

PIN ASSIGNMENT

Pin	Function
1	A1
2	B1
3	Y2
4	GND
5	A2
6	B2
7	Y1
8	V _{CC}

FUNCTION TABLE $Y = \overline{AB}$

Inp	outs Output				Inputs			
Α	В	Y						
L	L	Н						
L	Н	Н						
Н	L	Н						
Н	Н	L						

H = HIGH Logic Level L = LOW Logic Level

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

	Parameter	Symbol	Value	Unit
DC Supply Voltage		V _{CC}	-0.5 to +7.0	V
DC Input Voltage		VI	-0.5 to +7.0	V
DC Output Voltage		Vo	-0.5 to +7.0	V
DC Input Diode Current	V _I < GND	I _{IK}	-50	mA
DC Output Diode Current	V _O < GND	I _{OK}	-50	mA
DC Output Sink Current		I _O	±50	mA
DC Supply Current per Supply Pir	1	I _{CC}	±100	mA
DC Ground Current per Ground P	in	I _{GND}	±100	mA
Storage Temperature Range		T _{STG}	-65 to +150	°C
Lead Temperature, 1 mm from Ca	se for 10 Seconds	TL	260	°C
Junction Temperature under Bias		T_J	+ 150	°C
Thermal Resistance (Note 1)		$\theta_{\sf JA}$	250	°C/W
Power Dissipation in Still Air at 85	°C	P_{D}	250	mW
Moisture Sensitivity		MSL	Level 1	
Flammability Rating	Oxygen Index: 28 to 34	F _R	UL 94 V-0 @ 0.125 in	
ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	V _{ESD}	> 2000 > 200 N/A	V
Latchup Performance	Above V _{CC} and Below GND at 85°C (Note 5)	I _{Latchup}	±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- Tested to EIA/JESD22-A114-A.
 Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit	
Supply Voltage	Operating Data Retention Only	V _{CC}	1.65 1.5	5.5 5.5	V
Input Voltage (Note 6)		VI	0	5.5	V
Output Voltage	(HIGH or LOW State)	V _O	0	V _{CC}	V
Operating Free-Air Temperature		T _A	-40	+ 85	°C
Input Transition Rise or Fall Rate	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$ $V_{CC} = 3.0 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	Δt/ΔV	0 0 0	20 10 5	ns/V

^{6.} Unused inputs may not be left open. All inputs must be tied to a high- or low-logic input voltage level.

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	TA	_ = 25°C	;	-40°C ≤ 1	T _A ≤ 85°C	
Parameter	Condition	Symbol	(V)	Min	Тур	Max	Min	Max	Unit
High-Level Input Voltage		V _{IH}	1.65 2.3 to 5.5	0.75 V _{CC} 0.7 V _{CC}			0.75 V _{CC} 0.7 V _{CC}		V
Low-Level Input Voltage		V _{IL}	1.65 2.3 to 5.5			0.25 V _{CC} 0.3 V _{CC}		0.25 0.3 V _{CC}	V
High-Level Output Voltage V _{IN} = V _{IL} or V _{IH}	$I_{OH} = -100 \mu A$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$ $I_{OH} = -12 \text{ mA}$ $I_{OH} = -16 \text{ mA}$ $I_{OH} = -24 \text{ mA}$ $I_{OH} = -32 \text{ mA}$	V _{ОН}	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	V _{CC} 1.5 2.1 2.4 2.7 2.5 4.0		V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8		V
Low-Level Output Voltage V _{IN} = V _{IH} or V _{OH}	I _{OL} = 100 μA I _{OL} = 4 mA I _{OL} = 8 mA I _{OL} = 12 mA I _{OL} = 16 mA I _{OL} = 24 mA I _{OL} = 32 mA	V _{OL}	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5		0.0 0.08 0.20 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55		0.1 0.24 0.3 0.4 0.4 0.55 0.55	V
Input Leakage Current	$V_{IN} = V_{CC}$ or GND	I _{IN}	0 to 5.5			± 0.1		±1.0	μΑ
Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	Icc	5.5			1.0		10	μΑ

AC ELECTRICAL CHARACTERISTICS $t_R = t_F = 3.0 \text{ ns}$

		V _{cc}		T	_ = 25°C	;	-40°C ≤ 1	$T_A \leq 85^{\circ}C$	
Parameter	Condition	Symbol	(V)	Min	Тур	Max	Min	Max	Unit
Propagation Delay	$R_L = 1 M\Omega$, $C_L = 15 pF$	t _{PLH}	1.8 ± 0.15	2.0	5.7	10.5	2.0	11.0	ns
(Figure 3 and 4)		t _{PHL}	2.5 ± 0.2	1.2	3.2	5.3	1.2	5.7	
	$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$		3.3 ± 0.3	0.8	2.4	3.7	0.8	4.0	
	$R_L = 500 \ \Omega, C_L = 50 \ pF$			1.2	3.0	4.6	1.2	4.9	
	$R_L = 1 \text{ M}\Omega, C_L = 15 \text{ pF}$		5.0 ± 0.5	0.5	1.9	2.9	0.5	3.2	
	$R_L = 500 \ \Omega, C_L = 50 \ pF$			0.8	2.4	3.6	0.8	3.9	

CAPACITIVE CHARACTERISTICS

Parameter	Condition	Symbol	Typical	Unit
Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	C _{IN}	2.5	pF
Power Dissipation Capacitance (Note 7)	10 MHz, $V_{CC} = 3.3 \text{ V}$, $V_{I} = 0 \text{ V}$ or V_{CC} 10 MHz, $V_{CC} = 5.5 \text{ V}$, $V_{I} = 0 \text{ V}$ or V_{CC}	C _{PD}	9 11	pF

^{7.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

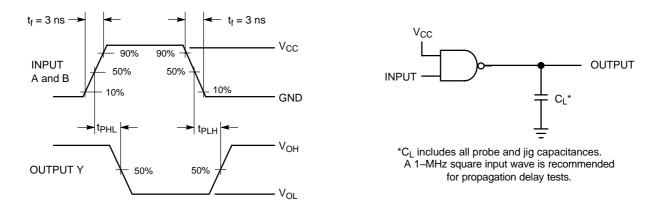


Figure 3. Switching Waveform

Figure 4. Test Circuit

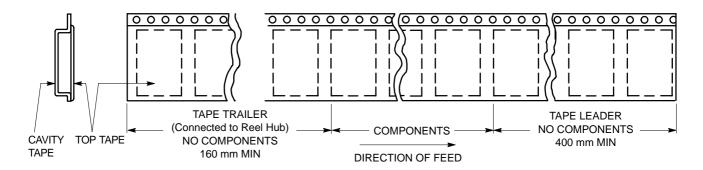


Figure 5. Tape Ends for Finished Goods

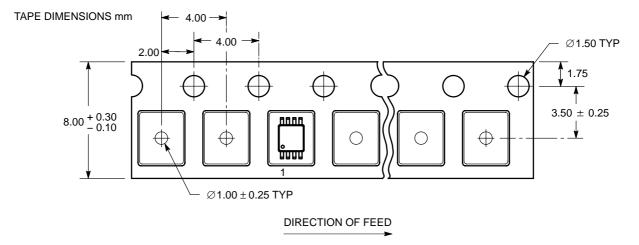


Figure 6. US8 Reel Configuration/Orientation

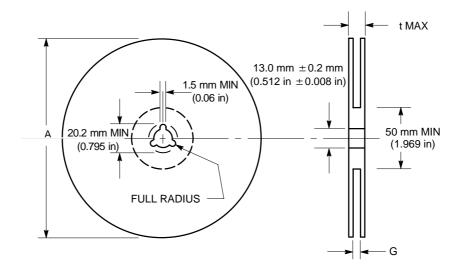


Figure 7. Reel Dimensions

REEL DIMENSIONS

Tape Size	T and R Suffix	A Max	G	t Max
8 mm	US	178 mm (7 in)	8.4 mm, + 1.5 mm, -0.0 (0.33 in + 0.059 in, -0.00)	14.4 mm (0.56 in)

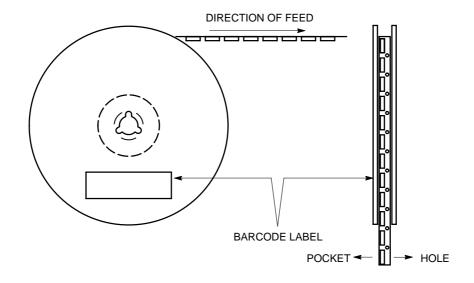


Figure 8. Reel Winding Direction

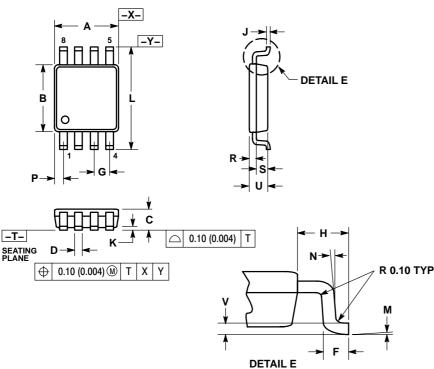
ORDERING INFORMATION

	Device Nomenclature							
Device	Logic Circuit Indicator	No. of Gates per Package	Temp Range Identifier	Technology	Device Function	Package Suffix	Package	Shipping [†]
NL27WZ00US	NL	0	7	WZ	00	US	US8	3000/Tape &
NL27WZ00USG	INL	2	,	VVZ	00	05	036	Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

US8 CASE 493-02 **ISSUE B**



NOTES

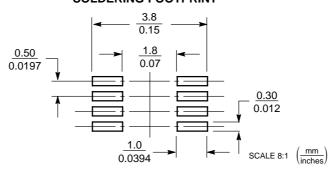
- NOTES:

 1. DIMENSIONING AND TOLERANCING PER
 ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSION "A" DOES NOT INCLUDE MOLD
 FLASH, PROTRUSION OR GATE BURR. FLASH, PROTRUSION OR GATE BURK.
 MOLD FLASH. PROTRUSION AND GATE
 BURR SHALL NOT EXCEED 0.140 MM
 (0.0055") PER SIDE.
 DIMENSION "B" DOES NOT INCLUDE
 INTER-LEAD FLASH OR PROTRUSION.
 INTER-LEAD FLASH AND PROTRUSION.
- SHALL NOT E3XCEED 0.140 (0.0055") PER SIDE.
- LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076-0.0203 MM.
- (300–800 ").
 ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 (0.0002 ").

DIM MIN MAX MIN MAX A 1.90 2.10 0.075 0.083 B 2.20 2.40 0.087 0.094 C 0.60 0.90 0.024 0.035
B 2.20 2.40 0.087 0.094
C 0.60 0.90 0.024 0.035
D 0.17 0.25 0.007 0.010
F 0.20 0.35 0.008 0.014
G 0.50 BSC 0.020 BSC
H 0.40 REF 0.016 REF
J 0.10 0.18 0.004 0.007
K 0.00 0.10 0.000 0.004
L 3.00 3.20 0.118 0.126
M 0° 6° 0° 6°
N 5° 10° 5° 10°
P 0.23 0.34 0.010 0.013
R 0.23 0.33 0.009 0.013
S 0.37 0.47 0.015 0.019
U 0.60 0.80 0.024 0.031
V 0.12 BSC 0.005 BSC

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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